



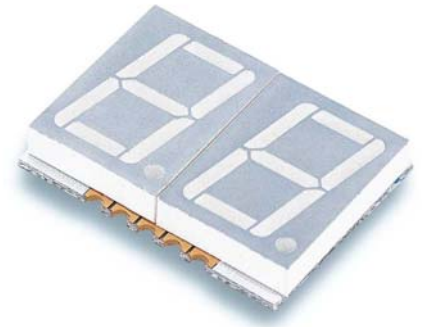
Technical Data Sheet

0.56" Dual Digit SMD Displays

ELSD-512SYGWA/S530-E2

Features

- Packaged in tape and reel for SMT manufacturing.
- Design flexibility(common cathode or anode).
- Categorized for luminous intensity.
- The thickness is thinner than tradition display.
- Pb free
- The product itself will remain with RoHS compliant version.



Descriptions

- The SMD type is much smaller than tradition type components, thus enable smaller board size, higher packing density, reduced storage space and finally smaller equipment to be obtained.

Applications

- Suitable for indoor use.
- Audio system.
- Set top box.
- Game machine.
- Channel indicator of TV.

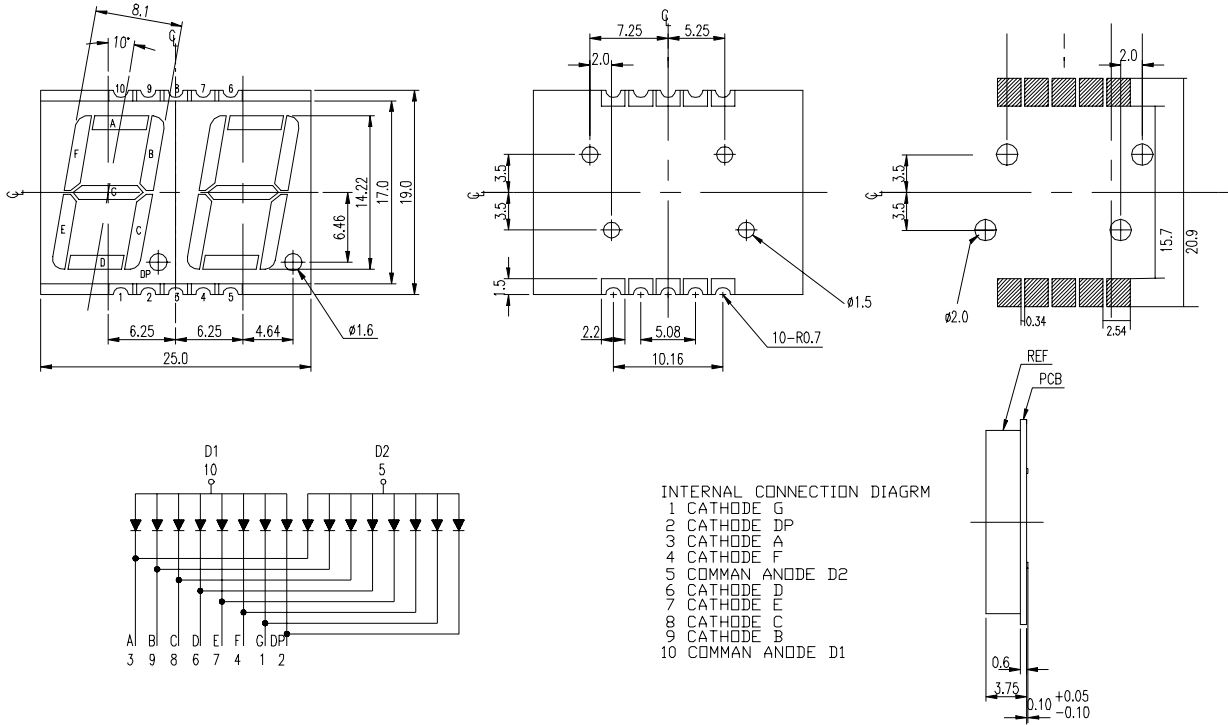
Device Selection Guide

Chip		Face Color
Material	Emitted Color	
AlGaInP	Brilliant Yellow Green	Gray

ELSD-512SYGWA/S530-E2

Land Pattern(Recommend)

Package Dimensions



Notes:

- All dimensions are in millimeters, tolerance is 0.25mm unless otherwise noted.
- Above specification may be changed without notice. Supplier will reserve authority on material change for above specification.

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Rating	Units
Forward Current	I_F	25	mA
Pulse Forward Current ^{*1}	I_{FP}	60	mA
Operating Temperature	T_{opr}	-40 ~ +85	°C
Storage Temperature	T_{stg}	-40 ~ +85	°C
Reflow Temperature	T_{ref}	260	°C
Electrostatic Discharge	ESD	2000	V
Power Dissipation	P_d	60	mW
Reverse Voltage	V_R	5	V

Notes: *1: I_{FP} Conditions--Pulse Width \leq 10msec and Duty \leq 1/10.

*2:Reflow time \leq 5 seconds.

Electro-Optical Characteristics (Ta=25°C)

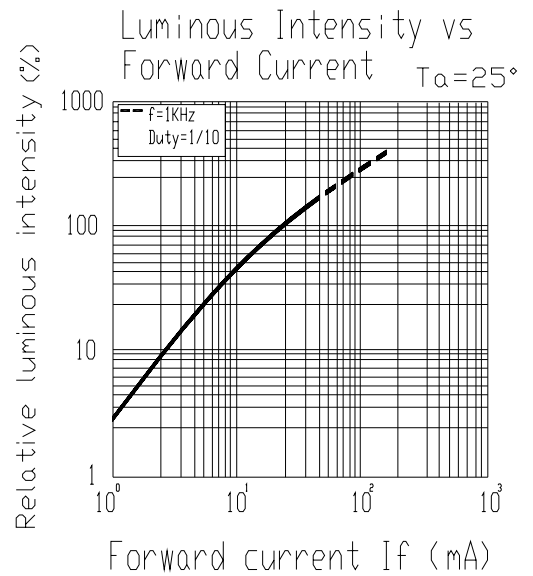
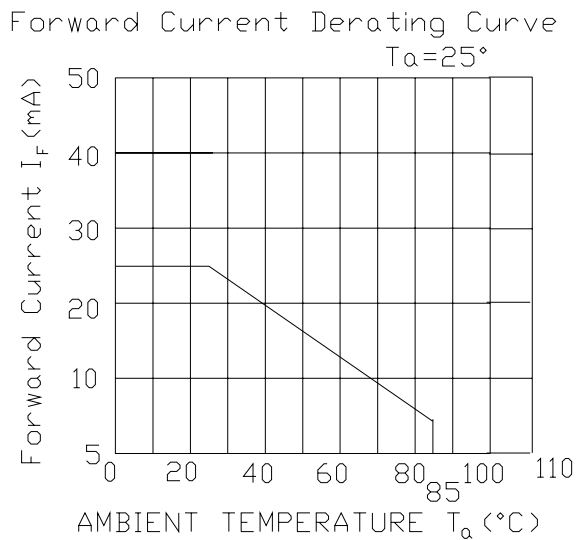
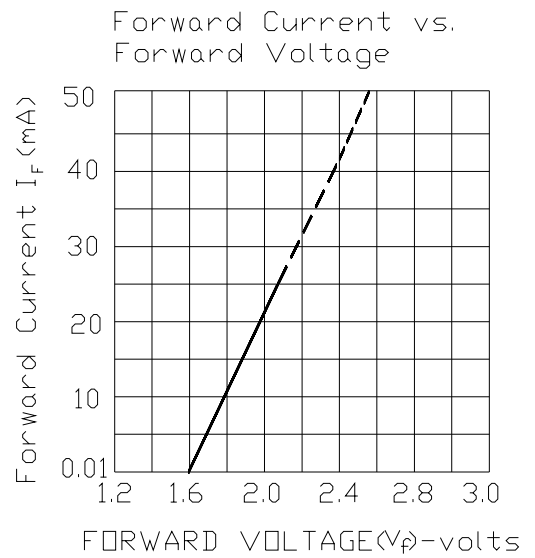
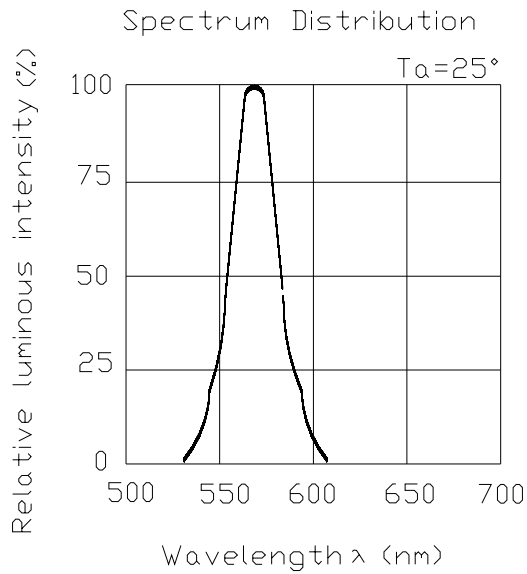
Parameter		Symbol	Min.	Typ.	Max.	Units	Condition
Forward Voltage		V_F	--	2.0	2.4	V	$I_F=20mA$
Reverse Current		I_R	--	--	10	μA	$V_R=5V$
Luminous Intensity	Per segment	I_V	4.0	9.6	--	mcd	$I_F=10mA$
	Per decimal point		2.0	3.9	--		
Peak Wavelength		λ_p	--	575	--	nm	$I_F=20mA$
Dominant Wavelength		λ_d	--	573	--	nm	$I_F=20mA$
Spectrum Radiation Bandwidth		$\Delta \lambda$	--	20	--	nm	$I_F=20mA$

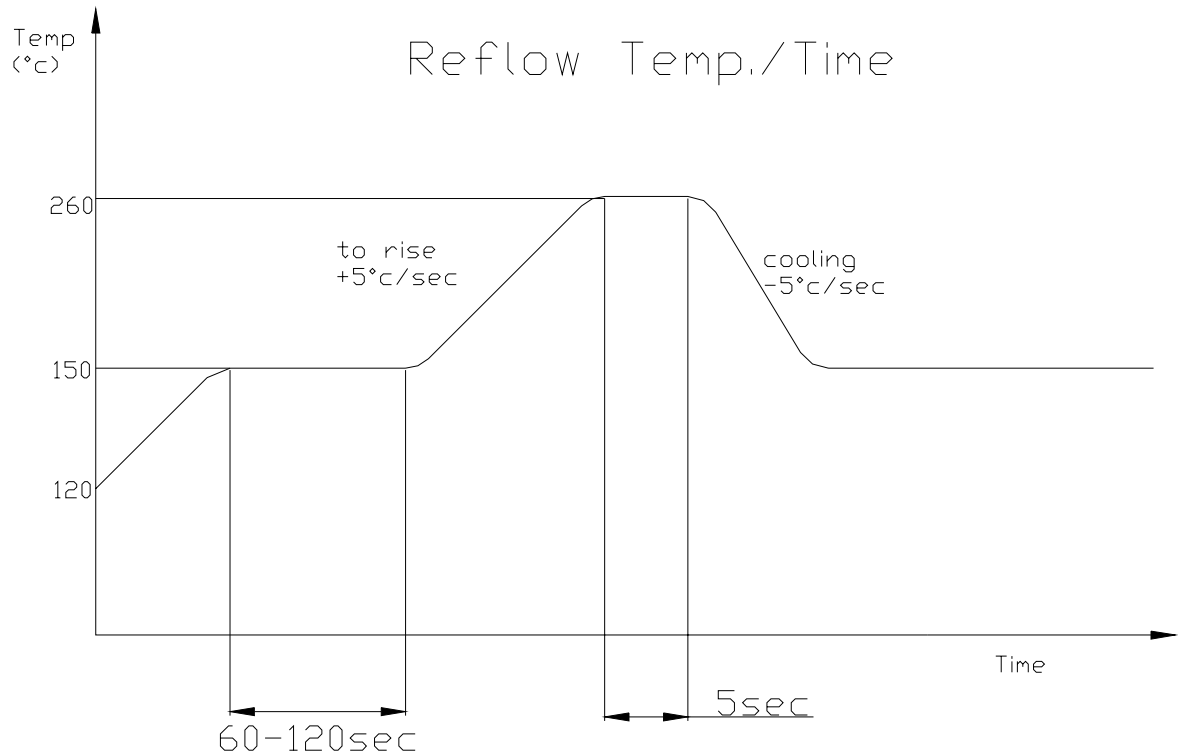
Chromaticity Coordinates Specifications for Bin Grading (Unit: mcd)

Rank	Min.	Max.	Rank	Min.	Max.
N	4.0	6.4	T	21.0	34.0
P	5.6	8.9	U	30.0	48.0
Q	7.8	12.5	V	42.0	67.0
R	11.0	17.6	W	59.0	94.0
S	15.0	24.0	---	---	---

Typical Electro-Optical Characteristics Curves

(SYG)



■ Reflow Temp. / Time :**■ Soldering Iron :**

Basic spec is ≤ 5 sec when 260°C. If temperature is higher, time should be shorter (+10°C → -1sec). Power dissipation of iron should be smaller than 15 W, and temperature should be controllable. Surface temperature of the device should be under 230 °C.

■ Rework :

1. Customer must finish rework within 5 sec under 260°C.
2. The head of iron can not touch copper foil.

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■ Reliability test items and conditions:

The reliability of products shall be satisfied with items listed below.

Confidence level : 90%

LTPD : 10%

NO	Item	Test Conditions	Test Hours/Cycle	Sample Size	Failure Judgment Criteria	Ac/Re
1	Reflow Soldering	TEMP:260°C±5°C Min. 5 SEC	6 Min	22 PCS	$I_v \leq I_{vt} * 0.5$ or $V_F \geq U$ or $V_F \leq L$	0/1
2	Temperature Cycle	H : +100°C 15min ∩ 5min L : -40°C 15min	300 CYCLES	22 PCS		0/1
3	Thermal Shock	H : +100°C 5min ∩ 10 sec L : -10°C 5min	300 CYCLES	22 PCS		0/1
4	High Temperature Storage	TEMP:100°C	1000 HRS	22PCS		0/1
5	Low Temperature Storage	TEMP:-40°C	1000 HRS	22 PCS		0/1
6	DC Operating Life	TEMP:25°C If = 10mA	1000 HRS	22 PCS		0/1
7	High Temperature / High Humidity	85°C / 85% RH	1000 HRS	22 PCS		0/1

Note : I_{vt} : The test I_v value of the chip before the reliability test

I_v : The test value of the chip that has completed the reliability test

U : Upper Specification Limit

L : Lower Specification Limit